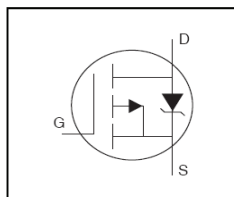


**Features**

- Advanced Planar Technology
- Low On-Resistance
- P-Channel MOSFET
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

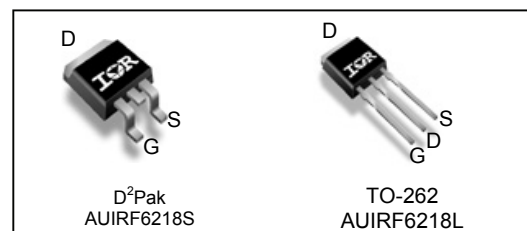


HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>-150V</b>
<b>R<sub>DS(on)</sub> max.</b>	<b>150mΩ</b>
<b>I<sub>D</sub></b>	<b>-27A</b>

**Description**

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF6218L	TO-262	Tube	50	AUIRF6218L
AUIRF6218S	D²-Pak	Tube	50	AUIRF6218S
		Tape and Reel Left	800	AUIRF6218STRL

**Absolute Maximum Ratings**

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	-27	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	-19	
I <sub>DM</sub>	Pulsed Drain Current ①	-110	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	250	W
	Linear Derating Factor	1.6	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ②	210	mJ
I <sub>AR</sub>	Avalanche Current ①	-16	A
dv/dt	Peak Diode Recovery ③	8.2	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case⑤	—	0.61	°C/W
R <sub>θJA</sub>	Junction-to-Ambient ( PCB Mount, steady state) ⑥	—	40	

HEXFET® is a registered trademark of Infineon.

\*Qualification standards can be found at [www.infineon.com](http://www.infineon.com)

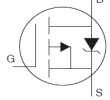
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	-0.17	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	120	150	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -16A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	-3.0	—	-5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Trans conductance	11	—	—	S	V <sub>DS</sub> = -50V, I <sub>D</sub> = -16A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-25	μA	V <sub>DS</sub> = -120V, V <sub>GS</sub> = 0V
		—	—	-250		V <sub>DS</sub> = -120V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 20V

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

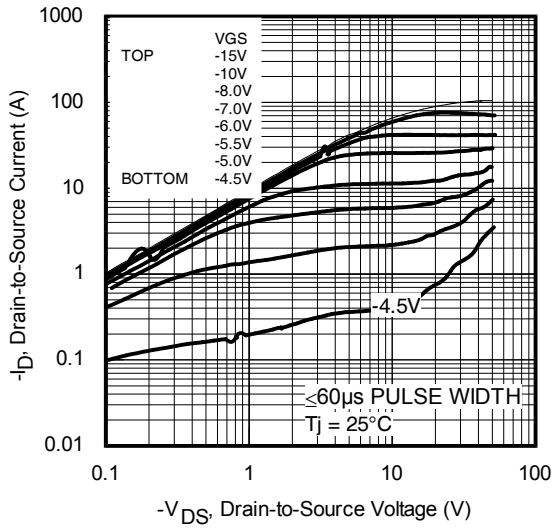
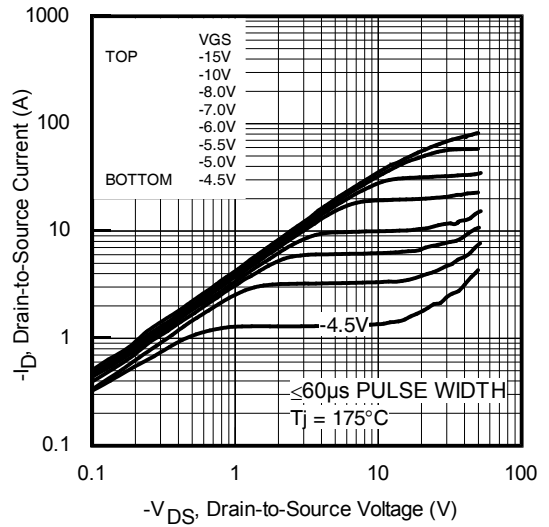
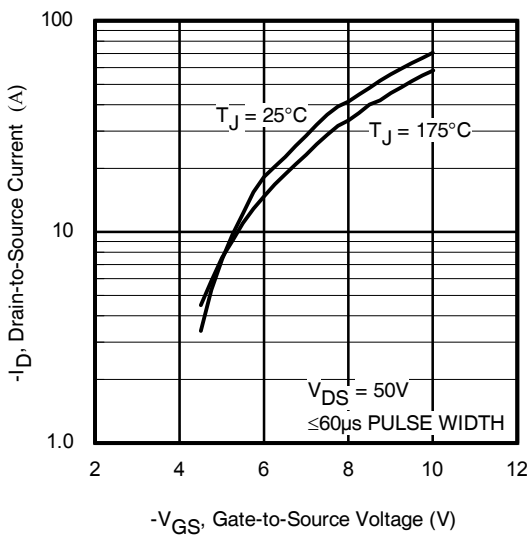
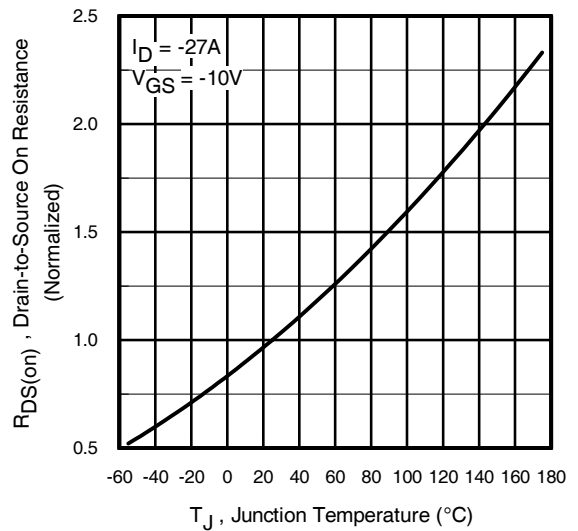
Q <sub>g</sub>	Total Gate Charge	—	71	110	nC	I <sub>D</sub> = -16A V <sub>DS</sub> = -120V V <sub>GS</sub> = -10V④
Q <sub>gs</sub>	Gate-to-Source Charge	—	21	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	32	—		
t <sub>d(on)</sub>	Turn-On Delay Time	—	21	—	ns	V <sub>DD</sub> = -75V I <sub>D</sub> = -16A R <sub>G</sub> = 3.9Ω, V <sub>GS</sub> = -10V④
t <sub>r</sub>	Rise Time	—	70	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	35	—		
t <sub>f</sub>	Fall Time	—	30	—		
C <sub>iss</sub>	Input Capacitance	—	2210	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = -25V f = 1.0MHz V <sub>GS</sub> = 0V, V <sub>DS</sub> = -1.0V, f = 1.0MHz V <sub>GS</sub> = 0V, V <sub>DS</sub> = -120V, f = 1.0MHz V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to -120V
C <sub>oss</sub>	Output Capacitance	—	370	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	89	—		
C <sub>oss</sub>	Output Capacitance	—	2220	—		
C <sub>oss</sub>	Output Capacitance	—	170	—		
C <sub>oss eff.</sub>	Effective Output Capacitance	—	340	—		

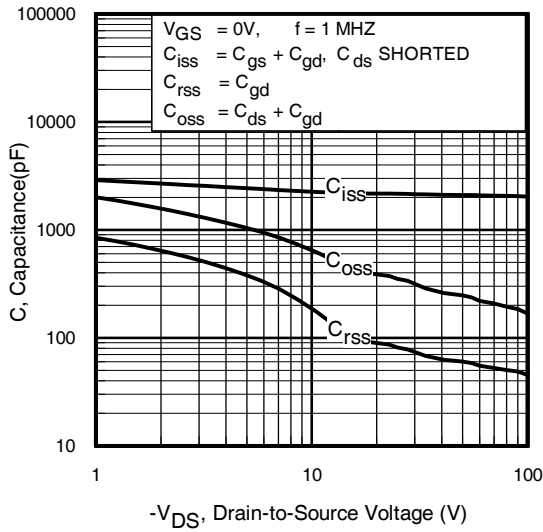
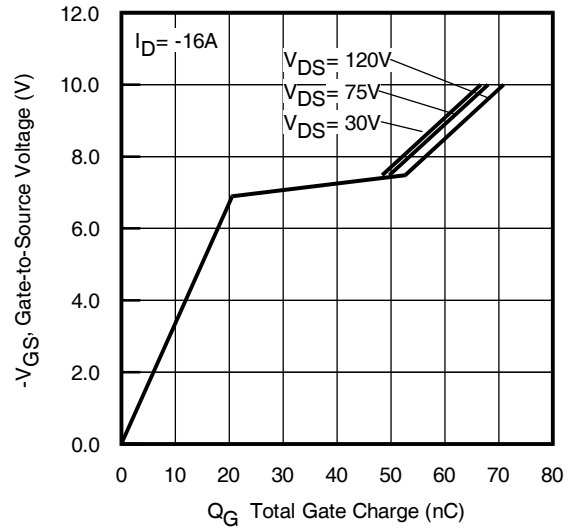
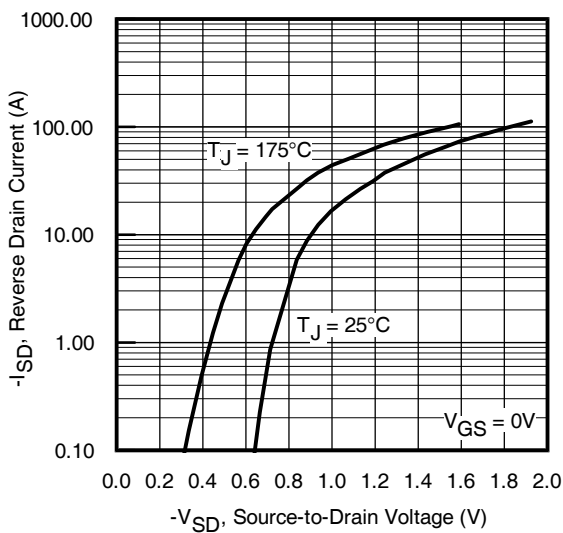
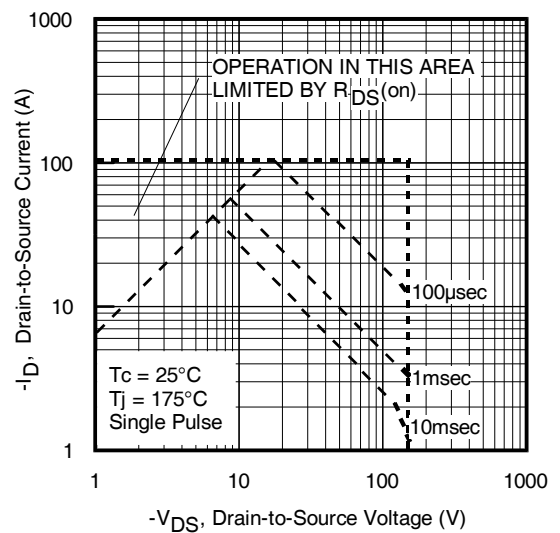
**Diode Characteristics**

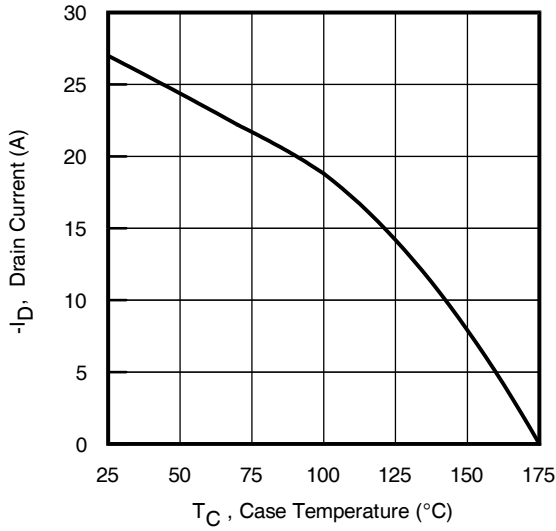
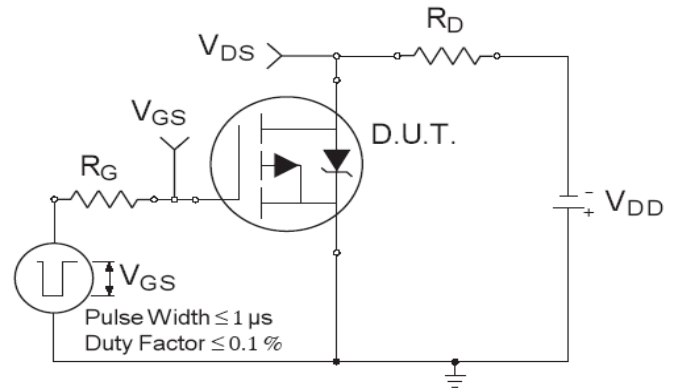
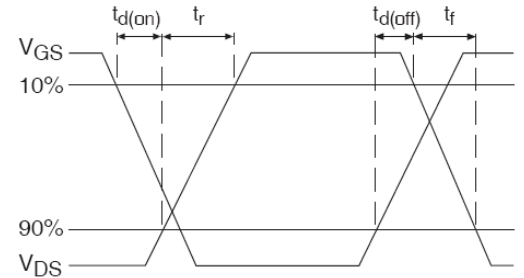
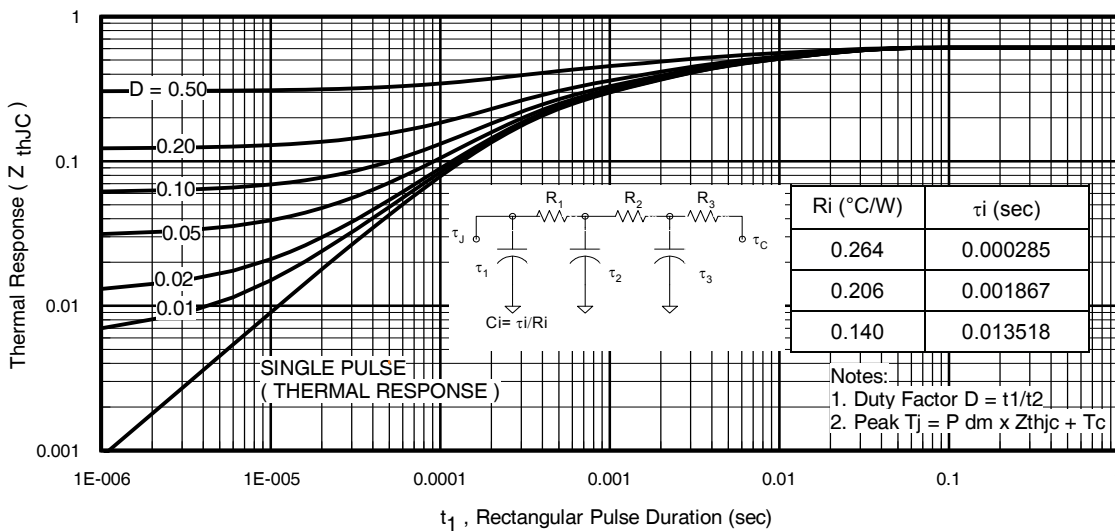
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-27	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-110		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.6	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -16A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	150	—	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -16A, V <sub>DD</sub> = -25V
Q <sub>rr</sub>	Reverse Recovery Charge	—	860	—	nC	di/dt = 100A/μs ④

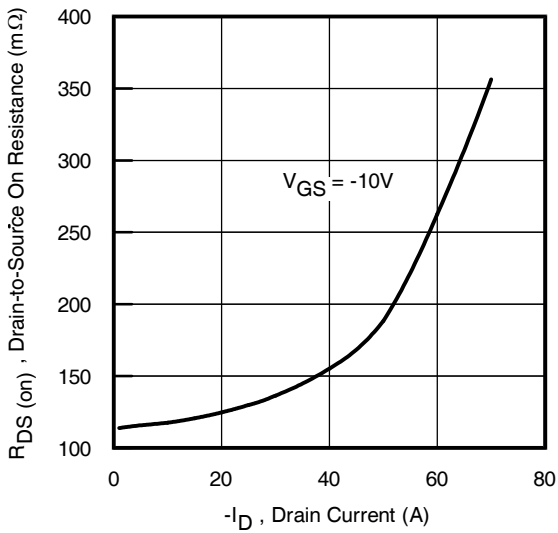
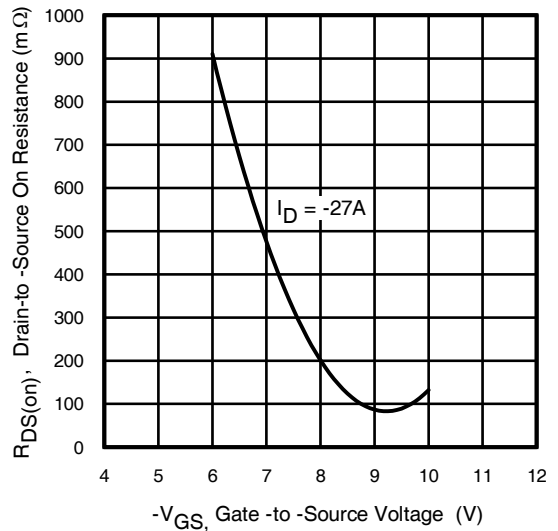
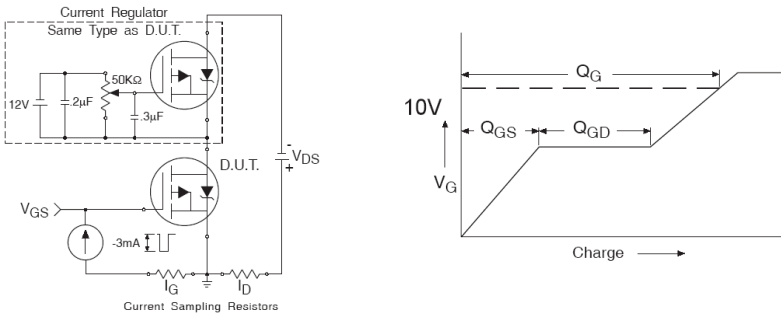
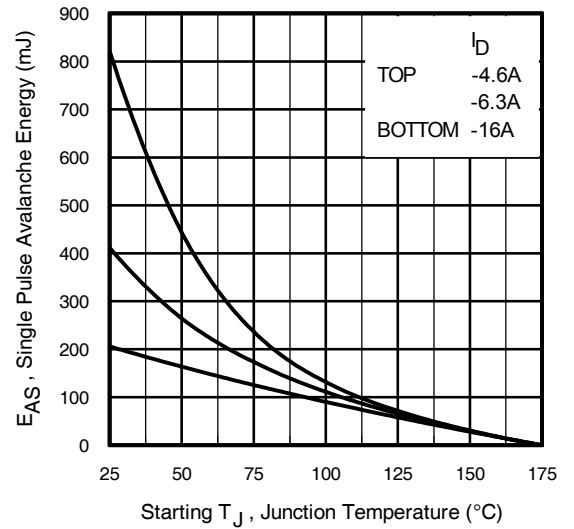
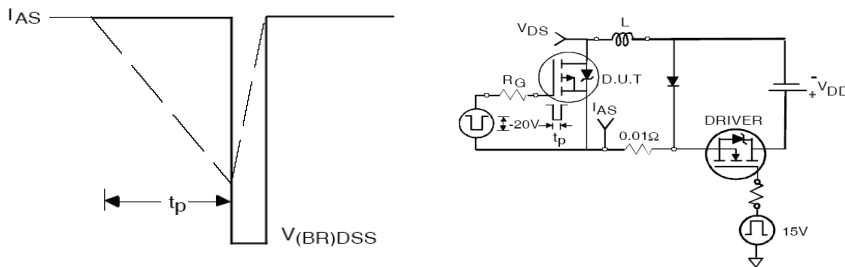
**Notes:**

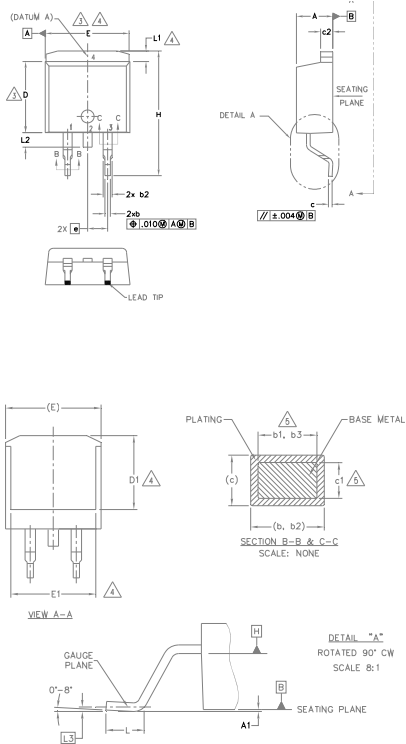
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T<sub>J</sub> = 25°C, L = 1.6mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = -17A.
- ③ I<sub>SD</sub> ≤ -17A, di/dt ≤ 520A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C
- ⑥ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994


**Fig. 1 Typical Output Characteristics**

**Fig. 2 Typical Output Characteristics**

**Fig. 3 Typical Transfer Characteristics**

**Fig. 4 Normalized On-Resistance vs. Temperature**


**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage

**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

**Fig. 7** Typical Source-to-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area


**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10a.** Switching Time Test Circuit

**Fig 10b.** Switching Time Waveforms

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig 12.** On-Resistance vs. Drain Current

**Fig 13.** On-Resistance vs. Gate Voltage

**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform

**Fig 15c.** Maximum Avalanche Energy vs. Drain Current

**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms

**D<sup>2</sup>Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))**


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
  6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  7. CONTROLLING DIMENSION: INCH.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.68	—	.066	4
L2	—	1.78	—	.070	
L3	0.25 BSC		.010 BSC		

**LEAD ASSIGNMENTS**
**DIODES**

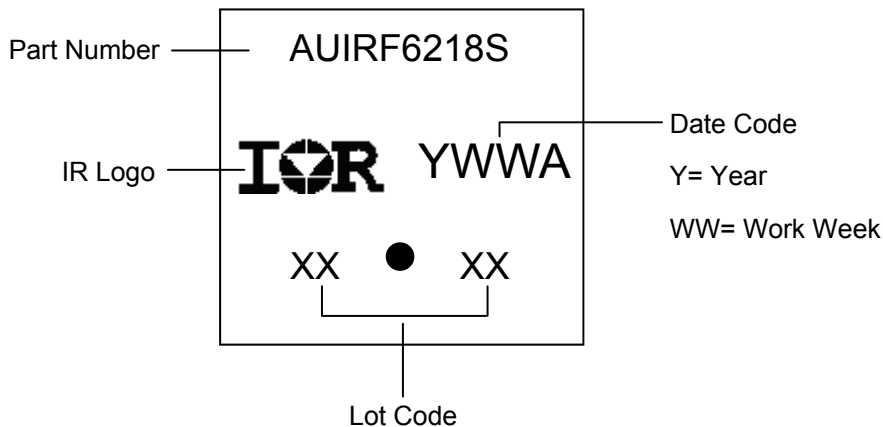
- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2.- CATHODE
- 3.- ANODE

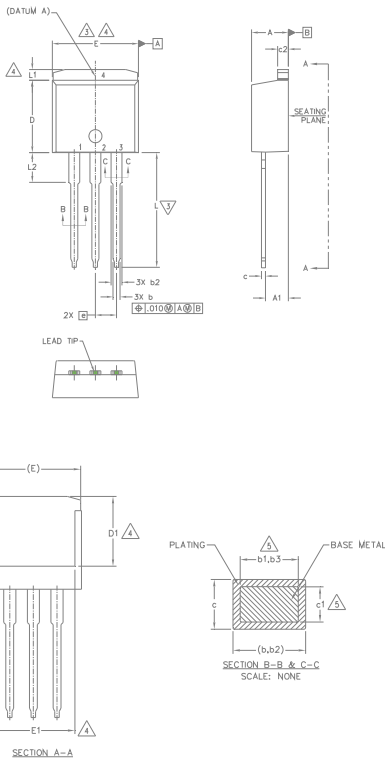
**HEXFET**

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

**D<sup>2</sup>Pak (TO-263AB) Part Marking Information**


**TO-262 Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

**LEAD ASSIGNMENTS**
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

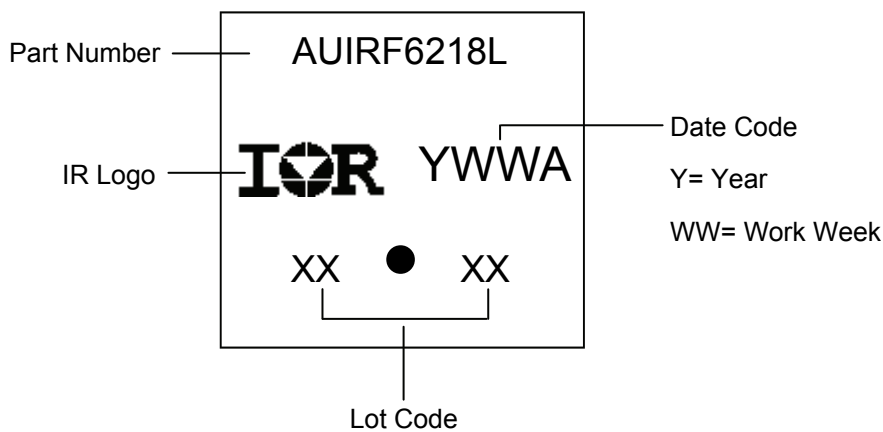
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

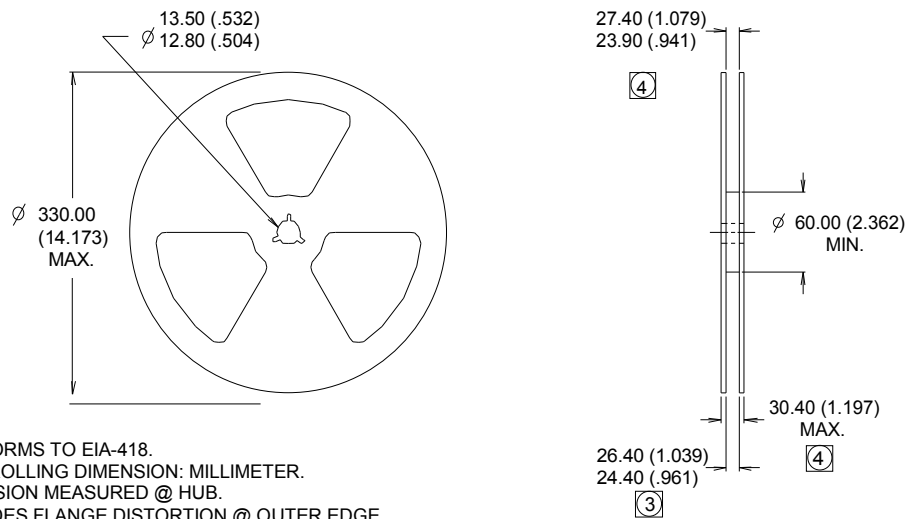
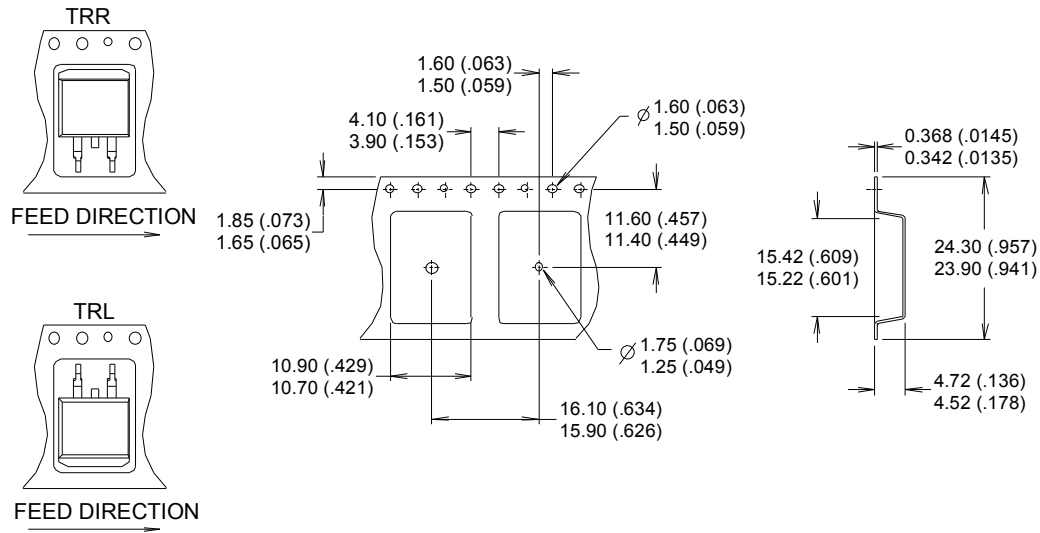
**DIODES**

- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	-	1.65	-	.065	4
L2	3.56	3.71	.140	.146	

**TO-262 Part Marking Information**




**D<sup>2</sup>Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))**


- NOTES :
1. COMFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DIMENSION MEASURED @ HUB.
  - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

**Qualification Information**

<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		D <sup>2</sup> -Pak	MSL1
		TO-262 Pak	
<b>ESD</b>	Machine Model	Class M4 (+/- 600V) <sup>†</sup> AEC-Q101-002	
	Human Body Model	Class H2 (+/- 3000V) <sup>†</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>†</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Highest passing voltage.

**Revision History**

Date	Comments
11/16/2015	<ul style="list-style-type: none"> <li>Updated datasheet with corporate template</li> <li>Corrected ordering table on page 1.</li> </ul>
10/10/2017	<ul style="list-style-type: none"> <li>Corrected typo error on part marking on page 7,8.</li> </ul>

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